ISLT1102 (Long Creepage)

DESCRIPTION

The ISLT1102 is an optically coupled isolator consisting of an infrared light emitting diode and an NPN silicon photo transistor. It belongs to Isocom's Long Creepage range of opto-couplers

FEATURES

- Wide Body Package
- AC Isolation test voltage 5000V_{RMS}
- Low coupling capacitance typically 0.3pF
- CTR selections available
- Wide temperature range
- Lead free
- Halogen Free
- UL Approval Pending

APPLICATIONS

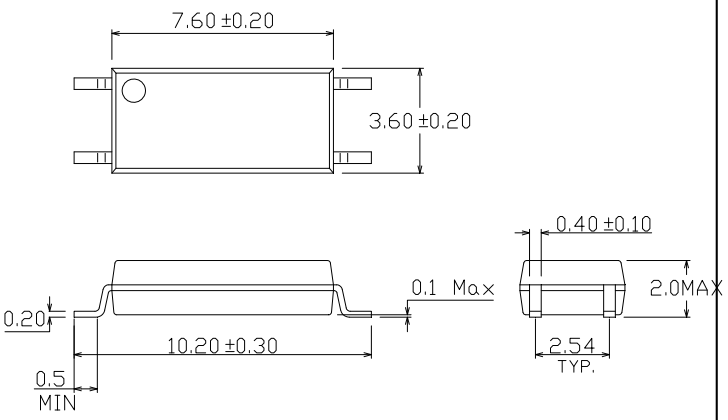
- Power Supply Feedback Voltage/Current
- Industrial system controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedance

ORDER INFORMATION

- Available in Tubes 100pieces per tube or Tape and Reel 2000 pieces per reel

MARKING INFORMATION

Please note that the device will be marked with the generic part number "ISLT1102" the date code will also be marked on the device.



ABSOLUTE MAXIMUM RATINGS

Input Diode

Forward Current	60mA
Reverse Voltage	6V
Power dissipation	100mW

Output Transistor

Collector to Emitter Voltage	80V
Emitter to Collector Voltage	7V
Collector Current	50mA
Power Dissipation	150mW

Total Package

Isolation test Voltage	5000V_{RMS}
Operating Temperature	-55 to 110 C
Storage Temperature	-55 to 150 C

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ELECTRICAL CHARACTERISTICS

Ambient Temperature = 25°C unless otherwise specified

INPUT

Parameter	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward Voltage	V_F	I_F = 50mA		1.45	1.50	V
Reverse Leakage	I_R	V_R = 6V			10	µA
Input Capacitance	C_{in}	V = 0V, f = 1 KHz		50		pF

OUTPUT

Parameter	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector—Emitter breakdown Voltage	BV_{CEO}	I_C = 100µA	80			V
Emitter—Collector breakdown Voltage	BV_{ECO}	I_E = 100µA	7			V
Collector dark Current	I_{CEO}	V_{CE} = 20V, I_F = 0mA			100	nA

COUPLED

Parameter	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	CTR	I_F = 10mA, V_{CE} = 5V	63		125	%
Collector—Emitter saturation Voltage	V_{CEsat}	I_F = 10mA, I_C = 1mA		0.1	0.3	V
Input to output isolation Voltage	V_{ISO}	See note 1	5000			V_{RMS}
Output rise time	t_r	V_{ce} =2V,Ic = 2mA, R_L = 100Ω		2.0	18	µS
Output fall time	t_f	V_{ce} =2V,Ic = 2mA, R_L = 100Ω		3.0	18	µS
Cut off frequency	f_c	I_F = 10mA, V_{CE} = 5V, R_L = 100Ω		100		kHz
Coupling Capacitance	C_k	f = 1 MHz		0.3		pF

Note 1 Measured with input leads shorted together and output leads shorted together

ISLT1102 (Long Creepage) Typical Curves

Figure 1. Forward Current vs. Forward Voltage

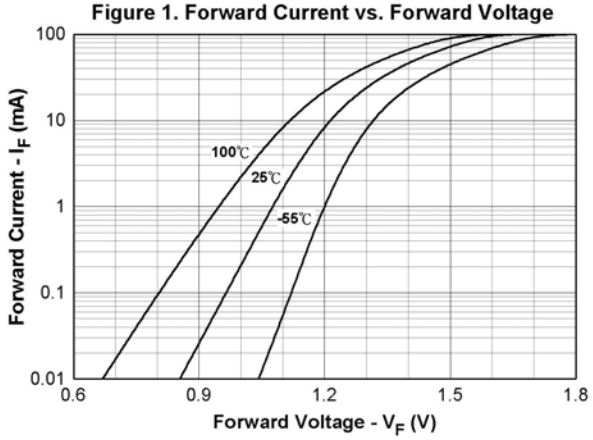


Figure.2 Collector Dark Current vs. Ambient Temperature

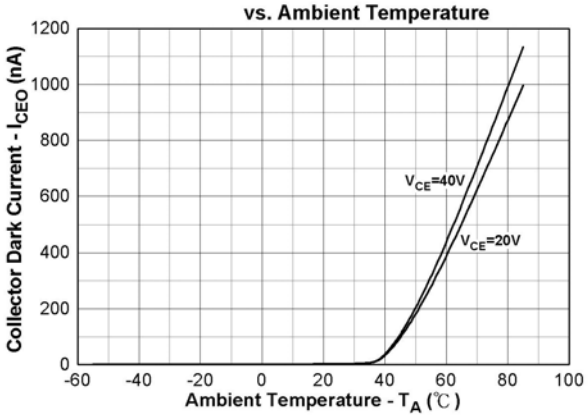


Figure 3. Collector Current vs. Collector Emitter Voltage

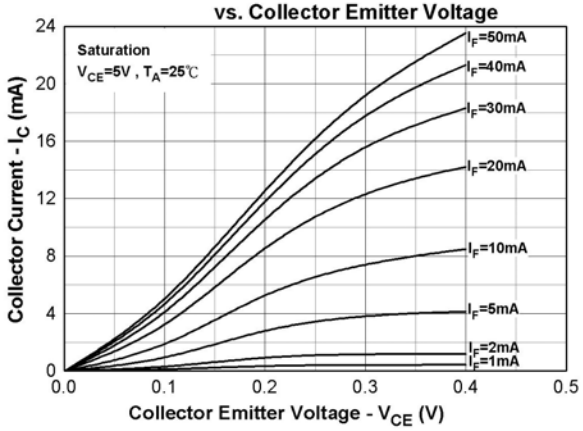


Figure 4. Collector Current vs. Collector Emitter Voltage

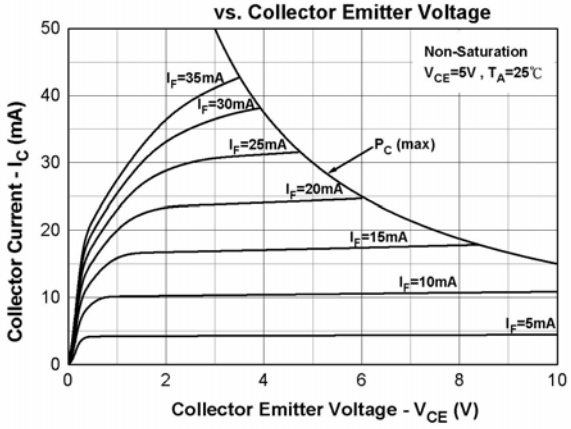


Figure 5. Normalized Collector Current vs. Forward Current

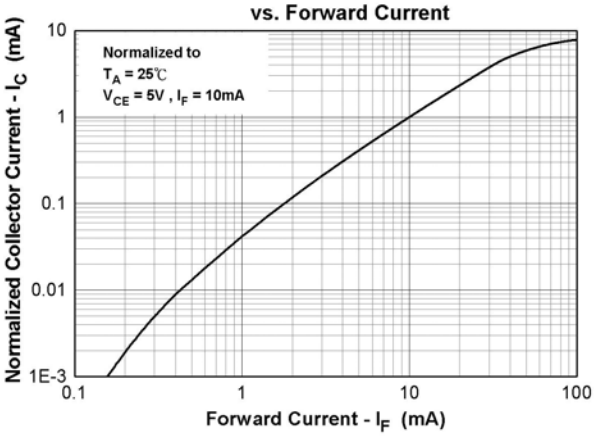
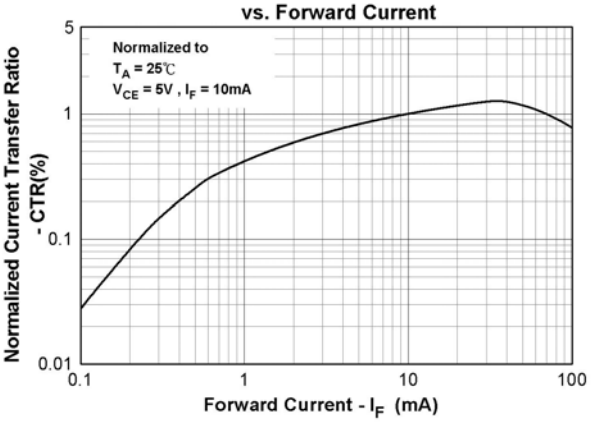


Figure 6. Normalized Current Transfer Ratio vs. Forward Current



ISLT1102 (Long Creepage) Typical Curves

Figure 7. Normalized Current Transfer Ratio vs. Ambient Temperature

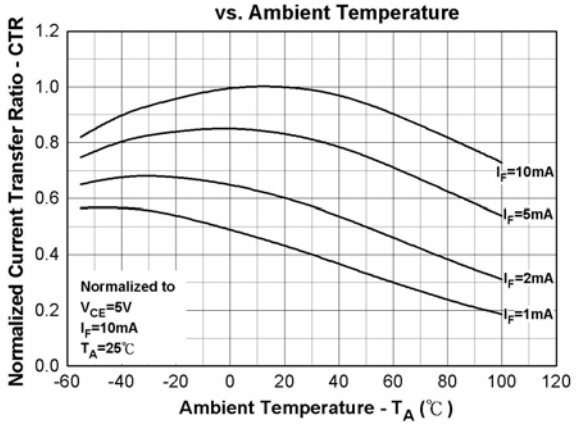


Figure 8. Normalized Current Transfer Ratio vs. Ambient Temperature

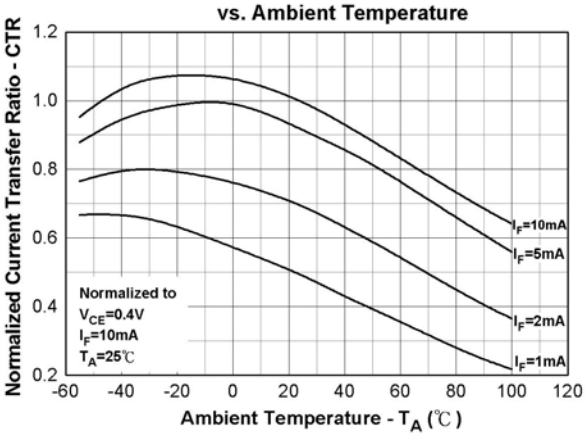


Figure 9. Turn on/off Time vs. Collector Current

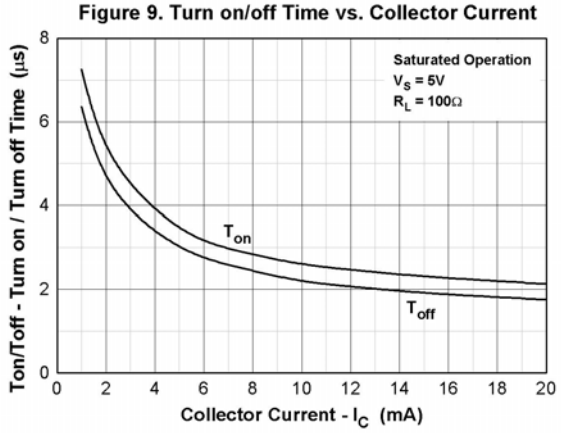
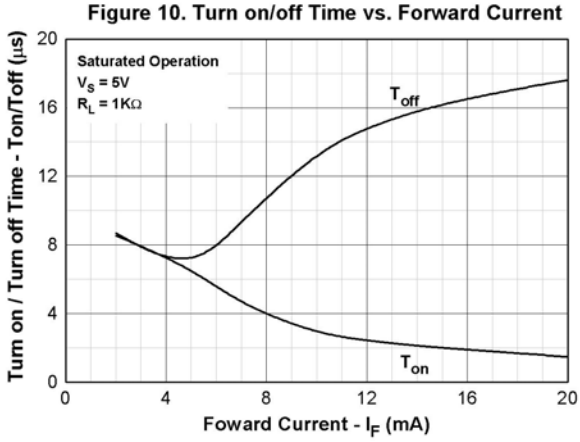


Figure 10. Turn on/off Time vs. Forward Current



Recommended pad layout for surface mount leadform